

Description

The SPD18P06PG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

General Features

 $V_{DS} = -60V I_{D} = -10 A$

 $R_{DS(ON)}$ < 140m Ω @ V_{GS} =10V

G S

Application

Brushless motor

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SPD18P06PG	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25 ℃ unless otherwise noted)

Symbol	Parameter Rating		Units	
Vos	Drain-Source Voltage	oltage -60		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20		
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-10	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹ -8.3		Α	
Ірм	Pulsed Drain Current ²	Pulsed Drain Current ² -26		
EAS	Single Pulse Avalanche Energy ³ 29.8		mJ	
las	Avalanche Current -24.4		A	
P _D @T _C =25°C	Total Power Dissipation ⁴ 31.3		W	
Тѕтс	Storage Temperature Range -55 to 150		°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R _θ JA	Thermal Resistance Junction-Ambient ¹	62	°C/W	
Reлc	Thermal Resistance Junction-Case ¹	se ¹ 4.0 °C/V		



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60		-	V	
$\triangle BV_{DSS}/\triangle T$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.049		V/°C	
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-8A		125	140	140 mΩ	
	Static Dialii-Source On-Resistance	V _{GS} =-4.5V , I _D =-6A		168	210	11122	
V _{GS(th)}	Gate Threshold Voltage	V -V I - 250uA	-1.0		-2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		5.42		mV/°C	
	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C			1	- uA	
I _{DSS}		V _{DS} =-48V , V _{GS} =0V , T _J =150°C			5		
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-5A		5.8		S	
Qg	Total Gate Charge (-4.5V)			5.85			
Q _{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-5A		2.9		nC	
Q _{gd}	Gate-Drain Charge			1.8			
T _{d(on)}	Turn-On Delay Time			10			
T _r	Rise Time	V_{DD} =-12V , V_{GS} =-10V , R_{G} =3.3 Ω ,		17		ns	
T _{d(off)}	Turn-Off Delay Time	I _D =-5A		22			
T _f	Fall Time			21			
C _{iss}	Input Capacitance			715			
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz		51		pF	
C _{rss}	Reverse Transfer Capacitance			34			
Is	Continuous Source Current ^{1,5}	V -V -0V Faras Ourset			-9.5	Α	
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			-24	Α	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V	
t _{rr}	Reverse Recovery Time			10.2		nS	
Qrr	Reverse Recovery Charge	lr=-8A,dl/dt=100A/μs,T _J =25°C		5.4		nC	

Note

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2. The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$
- 3. The EAS data shows Max. rating. The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.1mH, I_{AS} =-15A
- 4. The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

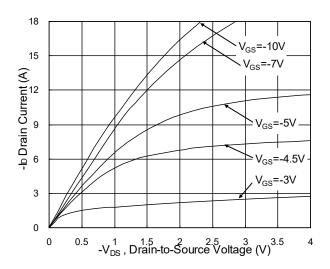


Fig.1 Typical Output Characteristics

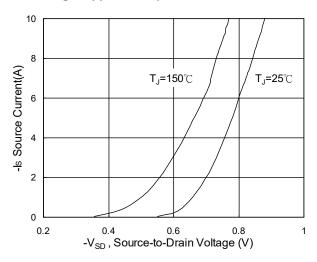


Fig.3 Forward Characteristics Of Reverse

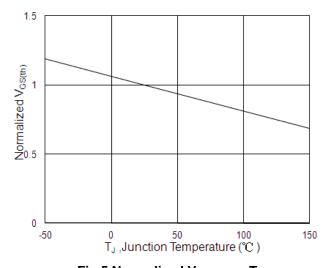


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

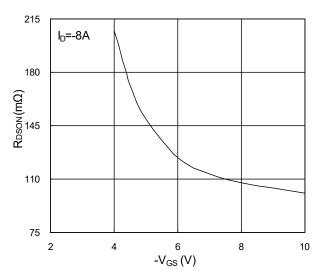


Fig.2 On-Resistance vs. G-S Voltage

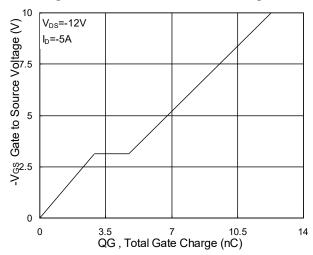


Fig.4 Gate-Charge Characteristics

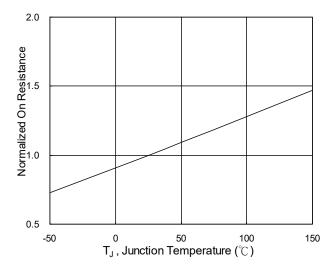
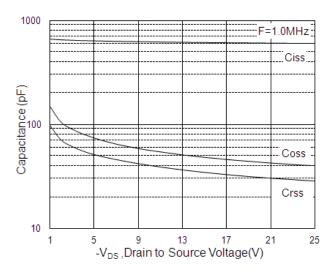


Fig.6 Normalized R_{DSON} vs. T_J



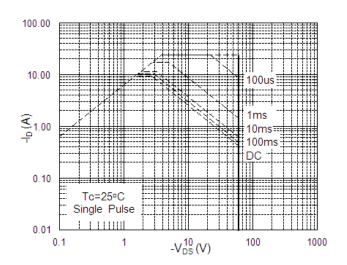


Fig.7 Capacitance

Fig.8 Safe Operating Area

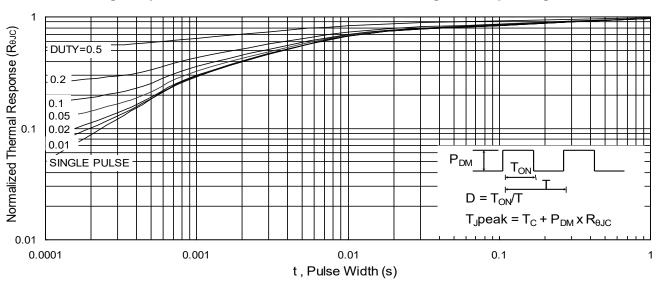
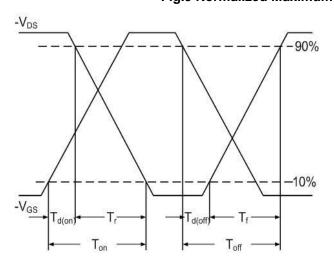


Fig.9 Normalized Maximum Transient Thermal Impedance



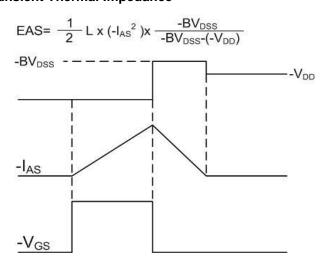
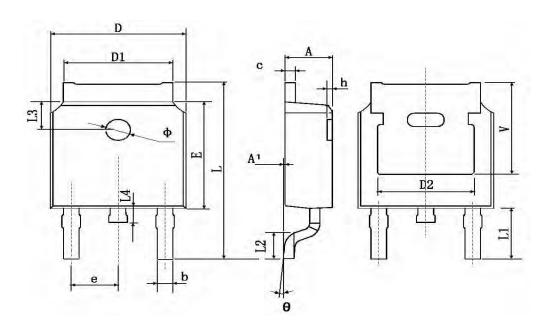


Fig.11 Unclamped Inductive Switching Waveform

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3		1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



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